

N-channel 100 V, 19 mΩ logic level MOSFET in LFPAK56 7 November 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

3. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	56	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	167	W
Static charac	teristics	· ·	· ·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>		-	14.6	19	mΩ
Dynamic cha	racteristics	·					
Q _{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 13}}{13}; \frac{\text{Fig. 14}}{14}$		-	14.1	-	nC

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4. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G C C C C C C C C C C C C C C C C C C C
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

5. Ordering information

Table 3. Ordering in	formation					
Type number	Package	ickage				
	Name	Description	Version			
BUK9Y19-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

6. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y19-100E	91910E

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	56	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	40	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	226	А

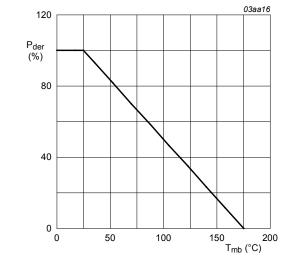
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	56	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	226	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 56 \; {\sf A}; {\sf V}_{sup} \le 100 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {}^\circ{\sf C}; \; unclamped; \\ & {\sf Fig. \; 4} \end{split}$	[3][4]	-	94.1	mJ

- [1]
- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

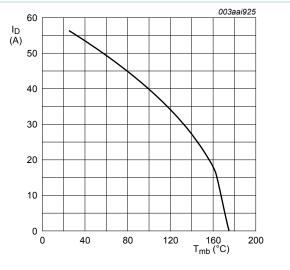
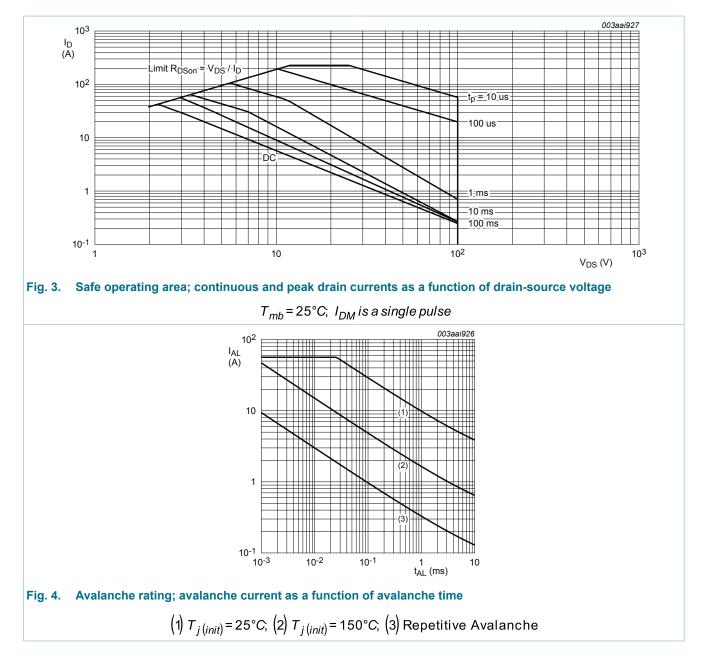


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$

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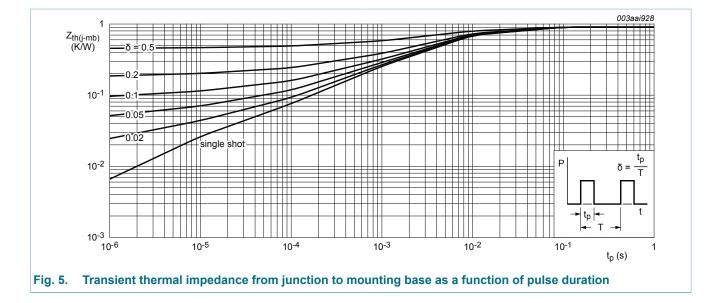
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8. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	0.9	K/W

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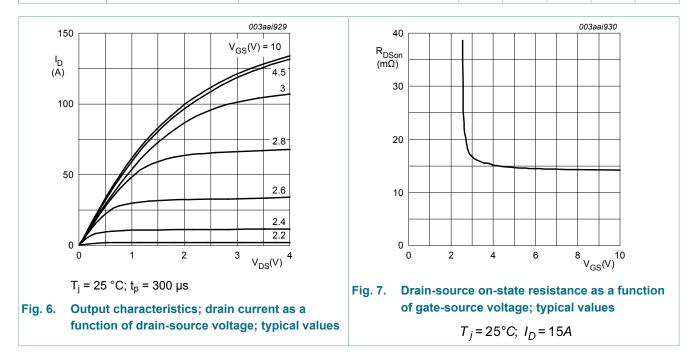
9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS} drain leakage	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.04	10	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	14	18	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	52.4	mΩ
Dynamic ch	aracteristics	· · ·				_,
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	39	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	8.5	-	nC
Q _{GD}	gate-drain charge		-	14.1	-	nC

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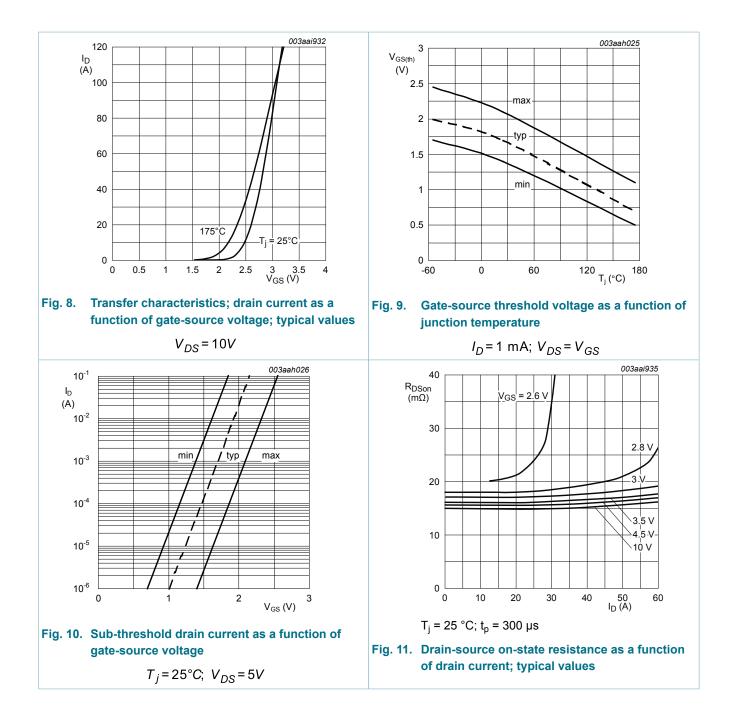
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;		-	3814	5085	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	222	266	pF
C _{rss}	reverse transfer capacitance			-	133	182	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 80 \text{ V}; \text{ R}_{L} = 5 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	18.5	-	ns
t _r	rise time			-	36.8	-	ns
t _{d(off)}	turn-off delay time			-	59.6	-	ns
t _f	fall time	-		-	34.3	-	ns
Source-dra	ain diode	1	1	1			
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	38	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C		-	56	-	nC



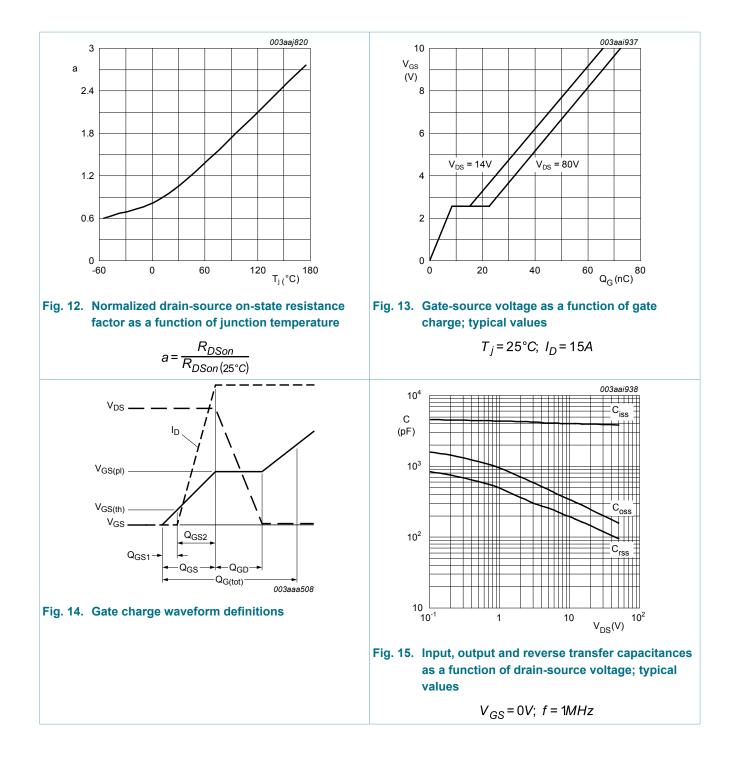
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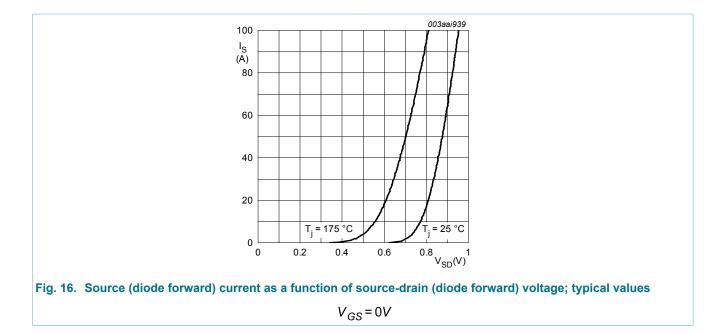
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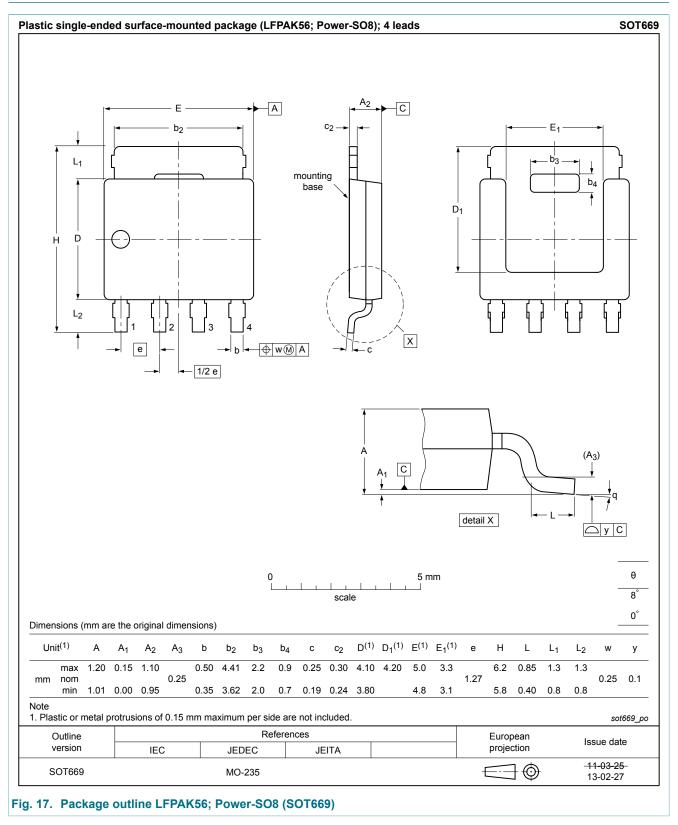
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10. Package outline



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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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